High Voltage Transistor

PNP Silicon

Features

• Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-100	Vdc
Collector – Emitter Voltage R_{BE} = 10 k Ω	V _{CER}	-110	Vdc
Collector Current – Continuous	۱ _C	-100	mAdc

THERMAL CHARACTERISTICS

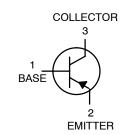
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board ⁽¹⁾ $T_A = 25^{\circ}C$	PD	225	mW
$T_A = 25 \text{ C}$ Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, ⁽²⁾ $T_A = 25^{\circ}C$	PD	300	mW
Derate above 25° C		2.4	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	– 55 to +150	°C

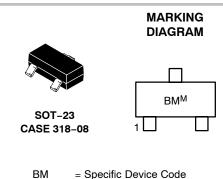
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



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M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
BSS63LT1	SOT-23	3000 / Tape & Reel
BSS63LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BSS63LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

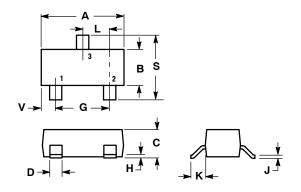
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage ($I_C = -100 \ \mu Adc$)	V _{(BR)CEO}	-100	_	_	Vdc
Collector – Emitter Breakdown Voltage (I_C = –10 µAdc, I_E = 0, R_{BE} = 10 k Ω)	V _{(BR)CER}	-110	_	_	Vdc
Collector – Base Breakdown Voltage ($I_E = -10 \ \mu Adc, I_E = 0$)	V _{(BR)CBO}	-110	_	_	Vdc
Emitter – Base Breakdown Voltage (I _E = –10 μAdc)	V _{(BR)EBO}	-6.0	_	_	Vdc
Collector Cutoff Current ($V_{CB} = -90$ Vdc, $I_E = 0$)	I _{CBO}	_	_	-100	nAdc
Collector Cutoff Current (V _{CE} = -110 Vdc, R _{BE} = 10 k Ω)	I _{CER}	_	_	-10	μAdc
Emitter Cutoff Current ($V_{EB} = -6.0 \text{ Vdc}, I_{C} = 0$)	I _{EBO}	_	_	-200	nAdc
ON CHARACTERISTICS				-	
DC Current Gain ($I_C = -10 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$) ($I_C = -25 \text{ mAdc}, V_{CE} = -1.0 \text{ Vdc}$)	h _{FE}	30 30			-
Collector – Emitter Saturation Voltage $(I_C = -25 \text{ mAdc}, I_B = -2.5 \text{ mAdc})$	V _{CE(sat)}	_	_	-250	mVdc
Base – Emitter Saturation Voltage ($I_c = -25 \text{ mAdc}, I_B = -2.5 \text{ mAdc}$)	V _{BE(sat)}	_	_	-900	mVdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = –25 mAdc, V _{CE} = –5.0 Vdc, f = 20 MHz)	f _T	50	95	_	MHz
Case Capacitance ($I_E = I_C = 0$, $V_{CB} = -10$ Vdc, f = 1.0 MHz)	C _C	_	_	20	pF

1. FR–5 = 1.0 \times 0.75 \times 0.062 in. 2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.

BSS63LT1

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AK**

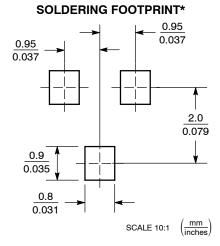


NOTES:

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.1102	0.1197	2.80	3.04
В	0.0472	0.0551	1.20	1.40
С	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
Н	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
к	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
v	0.0177	0.0236	0.45	0.60

STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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